

## Features

- $BV_{CEO} > -40V$
- $I_C = -200mA$  Collector Current
- Epitaxial Planar Die Construction
- Ultra-Small Surface Mount Package
- Complementary NPN Type: MMBT3904T
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

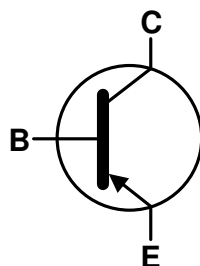
## Mechanical Data

- Case: SOT523
- Case Material: Molded Plastic. "Green" Molding Compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 ③
- Weight: 0.002 grams (Approximate)

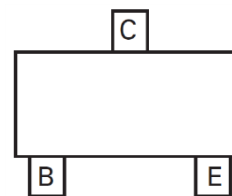
SOT523



Top View



Device Symbol



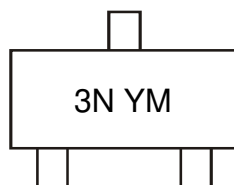
Pin-out Top View

## Ordering Information (Note 4)

Product	Status	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
MMBT3906T-7-F	Active	AEC-Q101	3N	7	8	3,000
MMBT3906T-13-F	Active	AEC-Q101	3N	13	8	10,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



3N = Product Type Marking Code  
 YM = Date Code Marking  
 Y or  $\bar{Y}$  = Year (ex: D = 2016)  
 M or  $\bar{M}$  = Month (ex: 9 = September)

### Date Code Key

Year	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	C	D	E	F	G	H	I	J	K	L	M

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Absolute Maximum Ratings** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	-40	V
Collector-Emitter Voltage	$V_{CEO}$	-40	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current	$I_C$	-200	mA

**Thermal Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	$P_D$	150	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	833	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

**ESD Ratings** (Note 6)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
- For a device mounted with the collector lead on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
  - Refer to JEDEC specification JESD22-A114 and JESD22-A115.

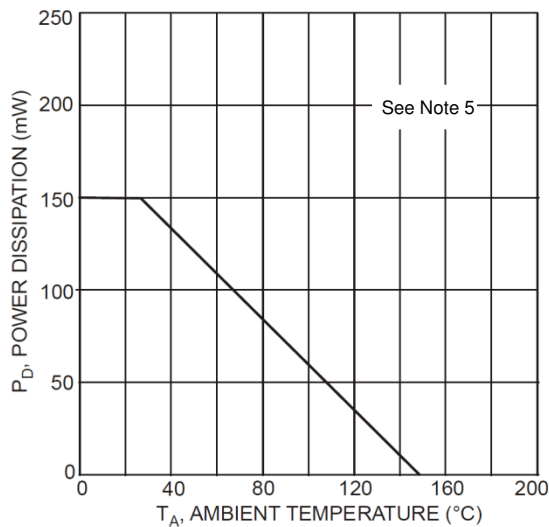
**Thermal Characteristics and Derating Information**


Fig. 1 Power Derating Curve

**Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$  unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition	
<b>OFF CHARACTERISTICS (Note 7)</b>						
Collector-Base Breakdown Voltage	$BV_{CBO}$	-40	—	V	$I_C = -10\mu\text{A}, I_E = 0$	
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	-40	—	V	$I_C = -1\text{mA}, I_B = 0$	
Emitter-Base Breakdown Voltage	$BV_{EBO}$	-5	—	V	$I_E = -10\mu\text{A}, I_C = 0$	
Collector Cutoff Current	$I_{CEX}$	—	-50	nA	$V_{CE} = -30\text{V}, V_{EB(OFF)} = -3\text{V}$	
Base Cutoff Current	$I_{BL}$	—	-50	nA	$V_{CE} = -30\text{V}, V_{EB(OFF)} = -3\text{V}$	
<b>ON CHARACTERISTICS (Note 7)</b>						
DC Current Gain	$h_{FE}$	60	—	—	$I_C = -100\mu\text{A}, V_{CE} = -1\text{V}$	
		80	—			$I_C = -1\text{mA}, V_{CE} = -1\text{V}$
		100	300			$I_C = -10\text{mA}, V_{CE} = -1\text{V}$
		60	—			$I_C = -50\text{mA}, V_{CE} = -1\text{V}$
		30	—			$I_C = -100\text{mA}, V_{CE} = -1\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	-0.25 -0.40	V	$I_C = -10\text{mA}, I_B = -1\text{mA}$ $I_C = -50\text{mA}, I_B = -5\text{mA}$	
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	-0.65	-0.85 -0.95	V	$I_C = -10\text{mA}, I_B = -1\text{mA}$ $I_C = -50\text{mA}, I_B = -5\text{mA}$	
<b>SMALL SIGNAL CHARACTERISTICS</b>						
Output Capacitance	$C_{obo}$	—	4.5	pF	$V_{CB} = -5\text{V}, f = 1.0\text{MHz}, I_E = 0$	
Input Capacitance	$C_{ibo}$	—	10	pF	$V_{EB} = -0.5\text{V}, f = 1.0\text{MHz}, I_C = 0$	
Input Impedance	$h_{ie}$	2	12	k $\Omega$	$V_{CE} = -10\text{V}, I_C = -10\text{mA}, f = 1.0\text{MHz}$	
Voltage Feedback Ratio	$h_{re}$	0.1	10	$\times 10^{-4}$		
Small Signal Current Gain	$h_{fe}$	100	400	—		
Output Admittance	$h_{oe}$	3	60	$\mu\text{S}$		
Current Gain-Bandwidth Product	$f_T$	250	—	MHz		$V_{CE} = -20\text{V}, I_C = -10\text{mA}, f = 100\text{MHz}$
Noise Figure	NF	—	5	dB	$V_{CC} = 5\text{V}, I_C = 100\mu\text{A}, R_S = 1\text{k}\Omega, f = 1\text{MHz}$	
<b>SWITCHING CHARACTERISTICS</b>						
Delay Time	$t_D$	—	35	ns	$V_{CC} = -3\text{V}, I_C = -10\text{mA}$	
Rise Time	$t_R$	—	35	ns	$V_{BE(OFF)} = -0.5\text{V}, I_{B1} = -1\text{mA}$	
Storage Time	$t_S$	—	225	ns	$V_{CC} = -3.0\text{V}, I_C = -10\text{mA}$	
Fall Time	$t_F$	—	75	ns	$I_{B1} = -I_{B2} = -1.0\text{mA}$	

Note: 7. Measured under pulsed conditions. Pulse width  $\leq 300\mu\text{s}$ . Duty cycle  $\leq 2\%$ .

**Typical Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

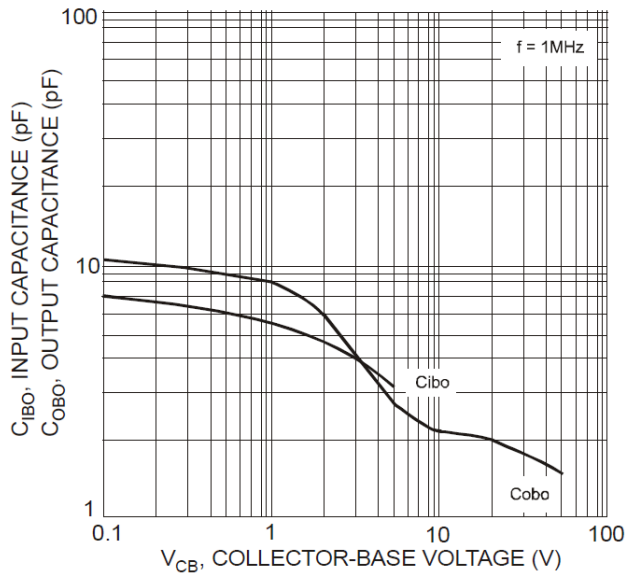


Fig. 2 Typical Input and Output Capacitance vs. Collector-Base Voltage

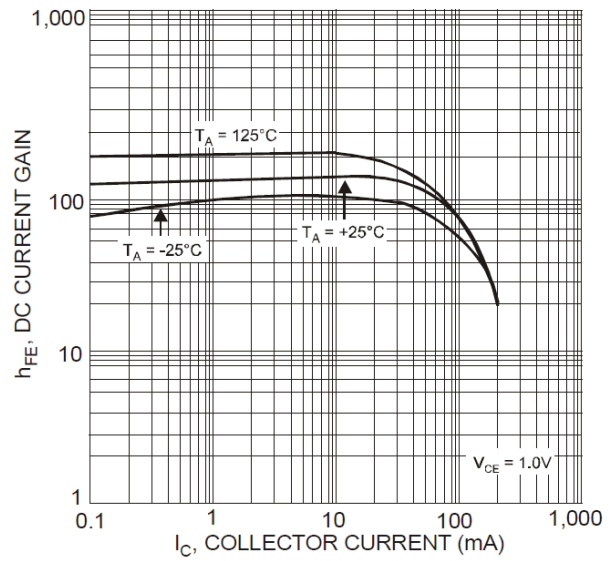


Fig. 3 Typical DC Current Gain vs. Collector Current

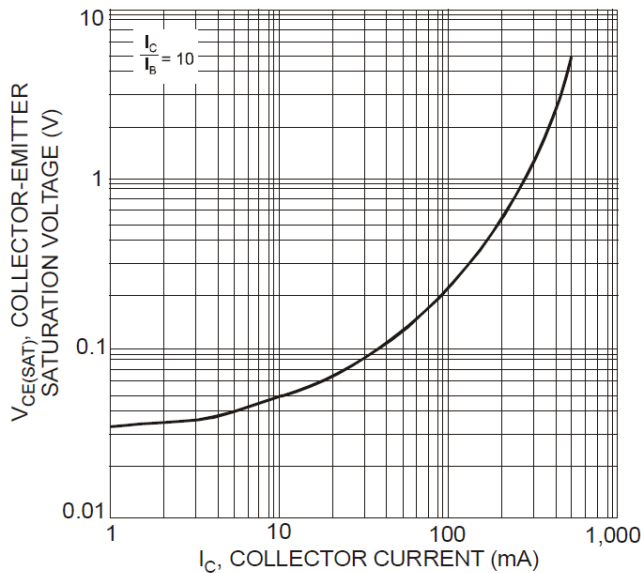


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

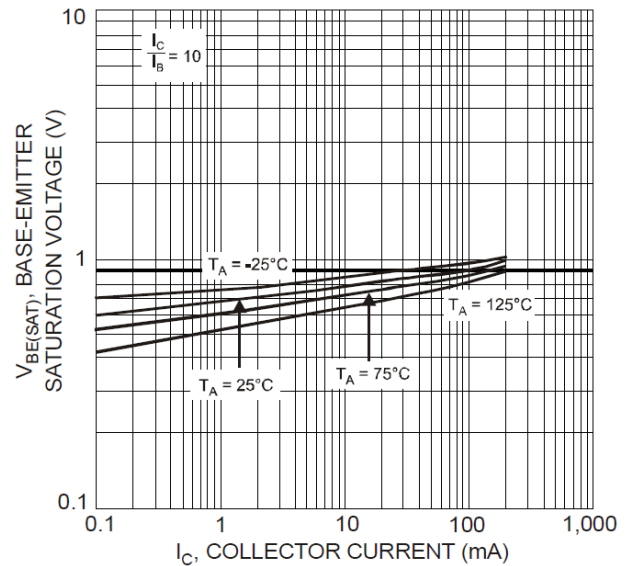
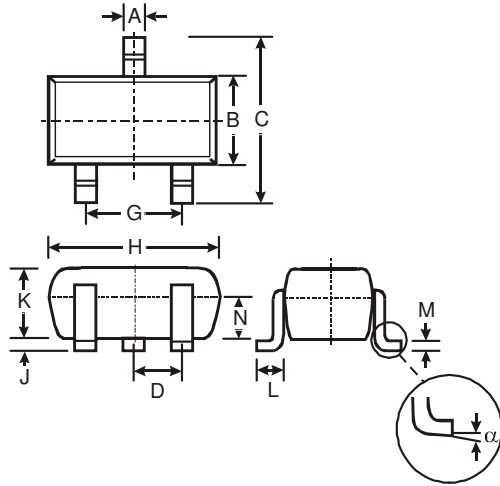


Fig. 5 Typical Base-Emitter Saturation Voltage vs. Collector Current

**Package Outline Dimensions**

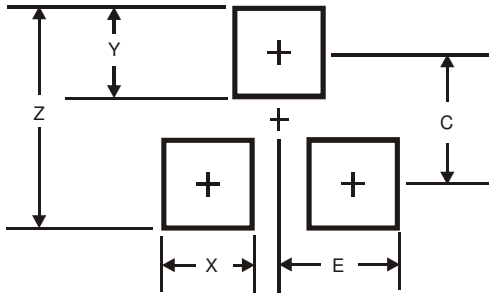
Please see <http://www.diodes.com/package-outlines.html> for the latest version.



SOT523			
Dim	Min	Max	Typ
A	0.15	0.30	0.22
B	0.75	0.85	0.80
C	1.45	1.75	1.60
D	—	—	0.50
G	0.90	1.10	1.00
H	1.50	1.70	1.60
J	0.00	0.10	0.05
K	0.60	0.80	0.75
L	0.10	0.30	0.22
M	0.10	0.20	0.12
N	0.45	0.65	0.50
$\alpha$	0°	8°	—
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.



Dimensions	Value (in mm)
Z	1.8
X	0.4
Y	0.51
C	1.3
E	0.7

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